

# 74LVX132

## LOW VOLTAGE CMOS QUAD 2-INPUT SCHMITT NAND GATE WITH 5V TOLERANT INPUTS

- HIGH SPEED: t<sub>PD</sub> = 5.9ns (TYP.) at V<sub>CC</sub> = 3.3V
- 5V TOLERANT INPUTS
- LOW POWER DISSIPATION:
- I<sub>CC</sub> = 2 μA (MAX.) at T<sub>A</sub>=25°C
- TYPICAL HYSTERESIS: 0.7V at V<sub>CC</sub> = 3.3V
- LOW NOISE:
  - $V_{OLP} = 0.3V$  (TYP.) at  $V_{CC} = 3.3V$
- SYMMETRICAL OUTPUT IMPEDANCE:
   |I<sub>OH</sub>| = I<sub>OL</sub> = 4mA (MIN)
- BALANCED PROPAGATION DELAYS:  $t_{PLH} \cong t_{PHL}$
- OPERATING VOLTAGE RANGE:
   V<sub>CC</sub>(OPR) = 2V to 3.6V (1.2V Data Retention)
- PIN AND FUNCTION COMPATIBLE WITH 74 SERIES 132
- IMPROVED LATCH-UP IMMUNITY
- POWER DOWN PROTECTION ON INPUTS

#### DESCRIPTION

The 74LVX132 is a low voltage CMOS QUAD 2-INPUT SCHMITT NAND GATE fabricated with sub-micron silicon gate and double-layer metal wiring  $C^2MOS$  technology. It is ideal for low power, battery operated and low noise 3.3V applications. Power down protection is provided on all inputs and 0 to 7V can be accepted on inputs with no regard to the supply voltage.





Table 1: Order Codes

PACKAGE	T & R
SOP	74LVX132MTR
TSSOP	74LVX132TTR

This device can be used to interface 5V to 3V system. It combines high speed performance with the true CMOS low power consumption.

Pin configuration and function are the same as those of the 74LVX00 but the 74LVX132 has hysteresis.

This together with its schmitt trigger function allows it to be used on line receivers with slow rise/fall input signals.

All inputs and outputs are equipped with protection circuits against static discharge, giving them 2KV ESD immunity and transient excess voltage.



#### Figure 2: Input Equivalent Circuit



#### **Table 2: Pin Description**

PIN N°	SYMBOL	NAME AND FUNCTION
1, 4, 9, 12	1A to 4A	Data Inputs
2, 5, 10, 13	1B to 4B	Data Inputs
3, 6, 8, 11	1Y to 4Y	Data Outputs
7	GND	Ground (0V)
14	V <sub>CC</sub>	Positive Supply Voltage

#### Table 3: Truth Table

A	В	Y
L	L	Н
L	Н	Н
Н	L	Н
Н	Н	L

57

#### **Table 4: Absolute Maximum Ratings**

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	Supply Voltage	-0.5 to +7.0	V
VI	DC Input Voltage	-0.5 to +7.0	V
Vo	DC Output Voltage	-0.5 to V <sub>CC</sub> + 0.5	V
Ι <sub>ΙΚ</sub>	DC Input Diode Current	- 20	mA
I <sub>OK</sub>	DC Output Diode Current	± 20	mA
۱ <sub>0</sub>	DC Output Current	± 25	mA
$\rm I_{CC}$ or $\rm I_{GND}$	DC V <sub>CC</sub> or Ground Current	± 50	mA
T <sub>stg</sub>	Storage Temperature	-65 to +150	°C
ΤL	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied.

#### **Table 5: Recommended Operating Conditions**

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	Supply Voltage (note 1)	2 to 3.6	V
VI	Input Voltage	0 to 5.5	V
Vo	Output Voltage	0 to V <sub>CC</sub>	V
T <sub>op</sub>	Operating Temperature	-55 to 125	°C

1) Truth Table guaranteed: 1.2V to 3.6V

#### **Table 6: DC Specifications**

		1	Test Condition		Value						
Symbol	Parameter	v <sub>cc</sub>		т	T <sub>A</sub> = 25°C		-40 to	85°C	-55 to 125°C		Unit
		(V)		Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
V <sub>t+</sub>	High Level Input Threshold	3.0				2.2		2.2		2.2	V
V <sub>t</sub> -	Low Level Input Threshold	3.0		0.9				0.9		0.9	V
V <sub>H</sub>	Hysteresis Voltage	3.0		0.3		1.2	0.3	1.2	0.3	1.2	V
V <sub>OH</sub>	High Level Output	2.0	I <sub>O</sub> =-50 μA	1.9	2.0		1.9		1.9		
	Voltage	3.0	I <sub>O</sub> =-50 μA	2.9	3.0		2.9		2.9		V
		3.0	I <sub>O</sub> =-4 mA	2.58			2.48		2.4		
V <sub>OL</sub>	Low Level Output	2.0	I <sub>O</sub> =50 μA		0.0	0.1		0.1		0.1	
	Voltage	3.0	I <sub>O</sub> =50 μA		0.0	0.1		0.1		0.1	V
		3.0	I <sub>O</sub> =4 mA			0.36		0.44		0.55	
I	Input Leakage Current	3.6	V <sub>I</sub> = 5V or GND			± 0.1		± 1		± 1	μΑ
I <sub>CC</sub>	Quiescent Supply Current	3.6	$V_{I} = V_{CC}$ or GND			2		20		20	μΑ

#### **Table 7: Dynamic Switching Characteristics**

			Test Condition		Value						
Symbol	Parameter	v <sub>cc</sub>		т	A = 25°	С	-40 to	85℃	-55 to	125°C	Unit
		(V)		Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
V <sub>OLP</sub>	Dynamic Low				0.3	0.5					
V <sub>OLV</sub>	Voltage Quiet Output (note 1, 2)	3.3		-0.5	-0.3						
V <sub>IHD</sub>	Dynamic High Voltage Input (note 1, 3)	3.3	C <sub>L</sub> = 50 pF	2.2							V
V <sub>ILD</sub>	Dynamic Low Voltage Input (note 1, 3)	3.3				0.9					

Worst case package.
 Max number of outputs defined as (n). Data inputs are driven 0V to 3.3V, (n-1) outputs switching and one output at GND.
 Max number of data inputs (n) switching. (n-1) switching 0V to 3.3V. Inputs under test switching: 3.3V to threshold (V<sub>ILD</sub>), 0V to threshold (V<sub>ILD</sub>), f=1MHz.



Table 8: AC Electrical	<b>Characteristics</b> (Input $t_r = t_f = 3ns$ )
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		٦	Test Condition		Value							
Symbol	Parameter	v <sub>cc</sub>	CL		Т	<sub>A</sub> = 25°	С	-40 to	85°C	-55 to	125°C	Unit
	(V)	(pĒ)		Min.	Тур.	Max.	Min.	Max.	Min.	Max.		
t <sub>PLH</sub> t <sub>PHL</sub>	Propagation Delay	2.7	15			7.5	10.5	1.0	12.0	1.0	12.0	
	Time	2.7	50			8.3	12.0	1.0	13.5	1.0	13.5	
		3.3 <sup>(*)</sup>	15			5.9	8.0	1.0	9.0	1.0	9.0	ns
		3.3 <sup>(*)</sup>	50			6.5	9.0	1.0	10.0	1.0	10.0	
t <sub>OSLH</sub>	Output To Output	2.7	50			0.5	1.0		1.5		1.5	
t <sub>OSHL</sub>	Skew Time (note1, 2)	3.3 <sup>(*)</sup>	50			0.5	1.0		1.5		1.5	ns

Skew is defined as the absolute value of the difference between the actual propagation delay for any two outputs of the same device switching in the same direction, either HIGH or LOW
 Parameter guaranteed by design

 (\*) Voltage range is 3.3V ± 0.3V

#### **Table 9: Capacitive Characteristics**

		Г	est Condition	Value							
Symbol	Symbol Parameter	v <sub>cc</sub>	V <sub>CC</sub>		T <sub>A</sub> = 25°C			-40 to 85°C		-55 to 125°C	
		V <sub>CC</sub> (V)		Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
C <sub>IN</sub>	Input Capacitance	3.3			6	10		10		10	pF
C <sub>PD</sub>	Power Dissipation Capacitance (note 1)	3.3			16						pF

1)  $C_{PD}$  is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation.  $I_{CC(opr)} = C_{PD} \times V_{CC} \times f_{IN} + I_{CC}/4$  (per gate)

#### Figure 3: Test Circuit



57

 $C_L$  =15/50pF or equivalent (includes jig and probe capacitance)  $R_T$  =  $Z_{OUT}$  of pulse generator (typically 50 $\Omega)$ 



Figure 4: Waveform - Propagation Delays (f=1MHz; 50% duty cycle)

DIM.		mm.			inch	
	MIN.	ТҮР	MAX.	MIN.	TYP.	MAX.
А	1.35		1.75	0.053		0.069
A1	0.1		0.25	0.004		0.010
A2	1.10		1.65	0.043		0.065
В	0.33		0.51	0.013		0.020
С	0.19		0.25	0.007		0.010
D	8.55		8.75	0.337		0.344
E	3.8		4.0	0.150		0.157
е		1.27			0.050	
Н	5.8		6.2	0.228		0.244
h	0.25		0.50	0.010		0.020
L	0.4		1.27	0.016		0.050
k	0°		8°	0°		8°



### SO-14 MECHANICAL DATA

DIM.		mm.		inch					
Divi.	MIN.	ТҮР	MAX.	MIN.	TYP.	MAX.			
А			1.2			0.047			
A1	0.05		0.15	0.002	0.004	0.006			
A2	0.8	1	1.05	0.031	0.039	0.041			
b	0.19		0.30	0.007		0.012			
С	0.09		0.20	0.004		0.0089			
D	4.9	5	5.1	0.193	0.197	0.201			
Е	6.2	6.4	6.6	0.244	0.252	0.260			
E1	4.3	4.4	4.48	0.169	0.173	0.176			
е		0.65 BSC			0.0256 BSC				
К	0°		8°	0°		8°			
L	0.45	0.60	0.75	0.018	0.024	0.030			

### TSSOP14 MECHANICAL DATA



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7/11

DIM.	mm.			inch		
	MIN.	ТҮР	MAX.	MIN.	TYP.	MAX.
А			330			12.992
С	12.8		13.2	0.504		0.519
D	20.2			0.795		
Ν	60			2.362		
Т			22.4			0.882
Ao	6.4		6.6	0.252		0.260
Во	9		9.2	0.354		0.362
Ko	2.1		2.3	0.082		0.090
Po	3.9		4.1	0.153		0.161
Р	7.9		8.1	0.311		0.319

1



DIM.	mm.			inch		
	MIN.	ТҮР	MAX.	MIN.	TYP.	MAX.
А			330			12.992
С	12.8		13.2	0.504		0.519
D	20.2			0.795		
Ν	60			2.362		
Т			22.4			0.882
Ao	6.7		6.9	0.264		0.272
Во	5.3		5.5	0.209		0.217
Ko	1.6		1.8	0.063		0.071
Po	3.9		4.1	0.153		0.161
Р	7.9		8.1	0.311		0.319





9/11

#### 74LVX132

#### Table 10: Revision History

Date	Revision	Description of Changes
27-Aug-2004 3		Ordering Codes Revision - pag. 1.



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